

74HC138

1-of-8 Decoder/ Demultiplexer

High-Performance Silicon-Gate CMOS

The 74HC138 is identical in pinout to the LS138. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC138 decodes a three-bit Address to one-of-eight active-low outputs. This device features three Chip Select inputs, two active-low and one active-high to facilitate the demultiplexing, cascading, and chip-selecting functions. The demultiplexing function is accomplished by using the Address inputs to select the desired device output; one of the Chip Selects is used as a data input while the other Chip Selects are held in their active states.

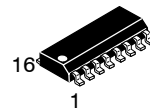
Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 100 FETs or 29 Equivalent Gates
- These are Pb-Free Devices

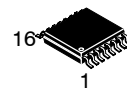
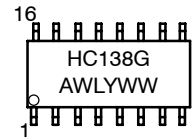


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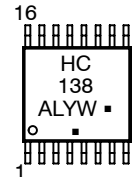
MARKING DIAGRAMS



SOIC-16
D SUFFIX
CASE 751B



TSSOP-16
DT SUFFIX
CASE 948F



HC138 = Device Code
A = Assembly Location
L, WL = Wafer Lot
Y = Year
W, WW = Work Week
G or ■ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

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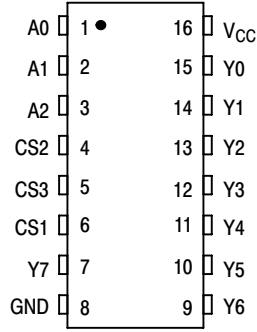


Figure 1. Pin Assignment

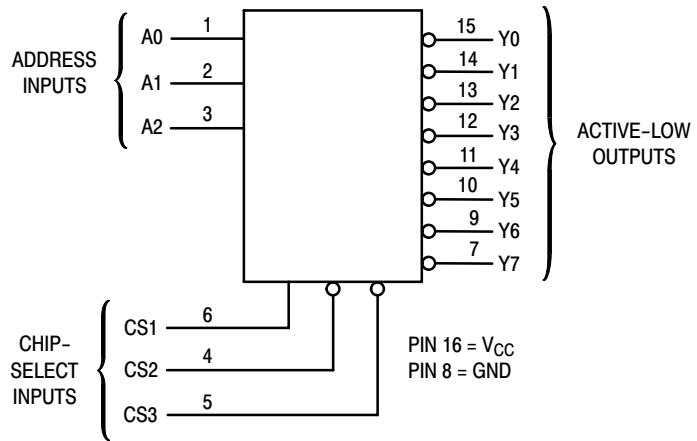


Figure 2. Logic Diagram

FUNCTION TABLE

Inputs			Outputs										
CS1	CS2	CS3	A2	A1	A0	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
X	X	H	X	X	X	H	H	H	H	H	H	H	H
X	H	X	X	X	X	H	H	H	H	H	H	H	H
L	X	X	X	X	X	H	H	H	H	H	H	H	H
H	L	L	L	L	L	L	H	H	H	H	H	H	H
H	L	L	L	L	H	H	L	H	H	H	H	H	H
H	L	L	L	H	L	H	H	L	H	H	H	H	H
H	L	L	L	H	H	H	H	L	H	H	H	H	H
H	L	L	H	L	H	H	H	H	H	L	H	H	H
H	L	L	H	H	L	H	H	H	H	H	L	H	H
H	L	L	H	H	H	H	H	H	H	H	H	L	L

H = high level (steady state); L = low level (steady state); X = don't care

ORDERING INFORMATION

Device	Package	Shipping [†]
74HC138DR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel
74HC138DTR2G	TSSOP-16*	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb-Free.

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MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	- 0.5 to $V_{CC} + 0.5$	V
V_{out}	DC Output Voltage (Referenced to GND)	- 0.5 to $V_{CC} + 0.5$	V
I_{in}	DC Input Current, per Pin	± 20	mA
I_{out}	DC Output Current, per Pin	± 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 50	mA
P_D	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T_{stg}	Storage Temperature	- 65 to + 150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds (SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating – SOIC Package: - 7 mW/°C from 65° to 125°C
TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	- 55	+ 125	°C
t_r, t_f	Input Rise and Fall Time (Figure 2)			ns
	$V_{CC} = 2.0 \text{ V}$	0	1000	
	$V_{CC} = 4.5 \text{ V}$	0	500	
	$V_{CC} = 6.0 \text{ V}$	0	400	

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DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} (V)	Guaranteed Limit			Unit
				-55°C to 25°C	≤ 85°C	≤ 125°C	
V _{IH}	Minimum High-Level Input Voltage	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	2.0	1.5	1.5	1.5	V
			3.0	2.1	2.1	2.1	
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
V _{IL}	Maximum Low-Level Input Voltage	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	2.0	0.5	0.5	0.5	V
			3.0	0.9	0.9	0.9	
			4.5	1.35	1.35	1.35	
			6.0	1.8	1.8	1.8	
V _{OH}	Minimum High-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{out} ≤ 20 μA	2.0	1.9	1.9	1.9	V
			4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		V _{in} = V _{IH} or V _{IL} I _{out} ≤ 2.4 mA I _{out} ≤ 4.0 mA I _{out} ≤ 5.2 mA	3.0	2.48	2.34	2.20	
			4.5	3.98	3.84	3.70	
			6.0	5.48	5.34	5.20	
V _{OL}	Maximum Low-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{out} ≤ 20 μA	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		V _{in} = V _{IH} or V _{IL} I _{out} ≤ 2.4 mA I _{out} ≤ 4.0 mA I _{out} ≤ 5.2 mA	3.0	0.26	0.33	0.40	
			4.5	0.26	0.33	0.40	
			6.0	0.26	0.33	0.40	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±0.1	±1.0	±1.0	μA
I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	6.0	4	40	40	μA

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6.0 ns)

Symbol	Parameter	V _{CC} (V)	Guaranteed Limit			Unit
			-55°C to 25°C	≤ 85°C	≤ 125°C	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 4)	2.0	135	170	205	ns
		3.0	90	125	165	
		4.5	27	34	41	
		6.0	23	29	35	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, CS1 to Output Y (Figures 2 and 4)	2.0	110	140	165	ns
		3.0	85	100	125	
		4.5	22	28	33	
		6.0	19	24	28	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, CS2 or CS3 to Output Y (Figures 3 and 4)	2.0	120	150	180	ns
		3.0	90	120	150	
		4.5	24	30	36	
		6.0	20	26	31	
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 2 and 4)	2.0	75	95	110	ns
		3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
C _{in}	Maximum Input Capacitance	-	10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

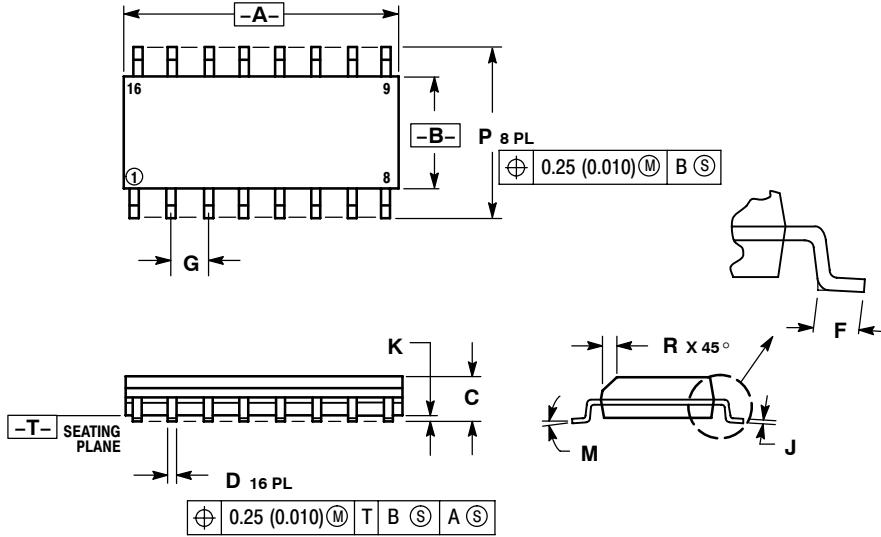
C _{PD}	Power Dissipation Capacitance (Per Package)*	Typical @ 25°C, V _{CC} = 5.0 V	
		55	
		pF	

* Used to determine the no-load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

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PACKAGE DIMENSIONS

SOIC-16
CASE 751B-05
ISSUE K

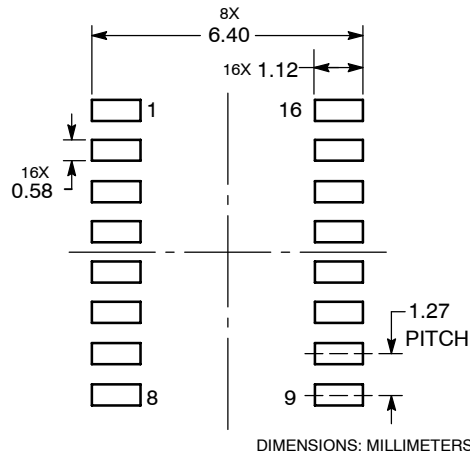


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.